



<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	Atty Docket No. NOVLP098	Application No.: 10/800,409
	Applicant: Wu et al.	
	Filing Date 03-11-2004	Group 1762

#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
BC	A1	6,867,086 B1	03.2005	Chen et al.			
	A2	6,903,004	06.2005	Spencer et al.			
	A3	6,232,658 B1	05.2001	Catabay et al.			
	A4	6,171,661	01.2001	Zheng et al.			
	A5	2002/0016085	02.2002	Huang et al.			
	A6	6,455,417	09.2002	Bao et al.			
	A7	7,018,918	03.2006	Kloster et al.			
	A8	6,849,549	02.2005	Chiou et al.			
	A9	2002/0141024 A1	10.2002	Retschke et al.			
	A10	2002/0064341 A1	05.2002	Fauver et al.			
	A11	7,094,713 B1	08.22.06	Niu et al.			
	A12	6,306,564	10.2001	Mullee, William H.			
	A13	2003/0066544 A1	04.2003	Jur et al.			
	A14	6,149,828 A	11.2000	Vaartstra, Brian A.			
	A15	6,943,121 B2	09.2005	Leu et al.			
	A16	2004/0102032 A1	05.2004	Kloster et al.			
	A17	2006/0110931 A1	05.2006	Fukazawa et al.			
	A18	7,087,271 B2	08.2006	Rhee et al.			
	A19	2006/0197881	09.2006	Kang et al.			
BC	A20	6,331,480	12.2001	Tsai et al.			

#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
BC	C1	U.S. Office Action mailed March 29, 2006, from U.S Application No. 10/800,377 [Atty Dkt No. NOVLP089/NVLS-002886].
	C2	U.S. Office Action mailed May 31, 2006, from U.S Application No. 10/941,502 [Atty Dkt No. NOVLP107/NVLS-2932].
	C3	U.S. Office Action mailed May 30, 2006, from U.S Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875].
	C4	U.S. Office Action mailed May 31, 2006, from U.S Application No. 10/849,568 [Atty Dkt No. NOVLP083/NVLS-2867].
BC	C5	U.S. Office Action mailed May 2, 2006, from U.S Application No. 11/050,621 [Atty Dkt No. NOVLP100/NVLS-2956].
Examiner /Bret Chen/		Date Considered 12/01/2006

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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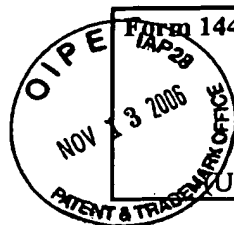
**U.S. Patent Documents**

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date

**Other Documents**

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
BC	C6	Kelman et al., "Method for Reducing Stress in Porous Dielectric Films", U.S. Application No. 11/369,311, filed March 6, 2006 (Atty Dkt: NOVLP154/NVLS-3121)
	C7	U.S. Office Action mailed June 28, 2006, from U.S Application No. 10/825,888 [Atty Dkt No. NOVLP088/NVLS-2882].
	C8	U.S. Office Action mailed May 2, 2006, from U.S Application No. 10/295,965.
	C9	U.S. Office Action mailed August 9, 2005, from U.S Application No. 10/295,965.
	C10	U.S. Office Action mailed June 14, 2006, from U.S Application No. 10/789,103 [Atty Dkt No. NOVLP094/NVLS-2919].
	C11	U.S. Office Action mailed September 8, 2006, from U.S Application No. 10/404,693 [Atty Dkt No. NOVLP064/NVLS-794].
	C12	U.S. Office Action mailed September 7, 2006, from U.S Application No. 10/820,525 [Atty Dkt No. NOVLP091/NVLS-2889].
BC	C13	U.S. Office Action mailed July 12, 2006, from U.S Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-2821].
Examiner /Bret Chen/		Date Considered 12/15/2006

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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**U.S. Patent Documents**

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date

**Other Documents**

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
BC	C1	Wu et al., "Methods for Fabricating High Hardness/Modules Low Dielectric Constant Materials," Novellus Systems, Inc., Appln No. 11/369,658, filed March 6, 2006, pp. 1-33. [NOVLP148/NVLS-3111]
BC	C2	Dhas et al., "Method of Reducing Defects in PECVD TEOS Films," Novellus Systems, Inc., Appln No. 11/396,303, filed March 30, 2006, pp. 1-21. [NOVLP160/NVLS-3168]
Examiner /Bret Chen/		Date Considered 12/01/2006

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.